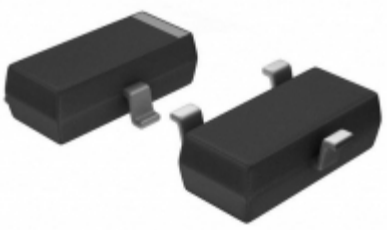


	<p>SI2331DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2331DS-T1-GE3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET P-CH 12V 3.2A SOT23-3</p>
	<p>Datenblätter:  SI2331DS-T1-GE3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, 42438 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2331DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 12V 3.2A SOT23-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	42438 pcs Stock
detaillierte Beschreibung	P-Channel 12V 3.2A (Ta) 710mW (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	710mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.2A (Ta)
Rds On (Max) @ Id, Vgs	48 mOhm @ 3.6A, 4.5V
VGS (th) (Max) @ Id	900mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	14nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	780pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI2331DS-T1-GE3 ist neu im Original, Suche SI2331DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2331DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2331DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2331DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 3.2A SOT23-3</p>	 <p>SI2333ADS-T1-GE3 VB SI2333ADS-T1-GE3 VB</p>	 <p>SI2331/SK2331A Original SOT-23</p>	 <p>SI2331DS VISHAY SI2331DS VISHAY</p>
 <p>SI2333CDS-T1-E3 Vishay / Siliconix MOSFET P-CH 12V 7.1A SOT23-3</p>	 <p>SI2331DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 3.2A SOT23-3</p>	 <p>SI2333-TP Micro Commercial Components (MCC) P-CHANNEL MOSFET, SOT-23 PACKAGE</p>	 <p>SI2333 SI SI2333 SI</p>

heiße Teile

Mehr

SI2323DS-T1-GE3	SI2323DS-T1-GE3	SI2324DS-T1-E3	SI2324DS-T1-GE3	SI2324DS-T1-GE3
SI2325DS-T1-E3	SI2325DS-T1-E3	SI2325DS-T1-GE3	SI2325DS-T1-GE3	SI2327DS-T1-E3
SI2327DS-T1-E3	SI2327DS-T1-GE3	SI2327DS-T1-GE3	SI2328DS	SI2328DS-T1
SI2328DS-T1-E3	SI2328DS-T1-E3	SI2328DS-T1-GE3	SI2328DS-T1-GE3	SI2329DS-T1-E3
SI2329DS-T1-GE3	SI2329DS-T1-GE3	SI2331DS	SI2331DS-T1-E3	SI2331DS-T1-E3
SI2331DS-T1-GE3	SI2333ADS-T1-GE3	SI2333CDS	SI2333CDS-T1-E3	SI2333CDS-T1-E3
SI2333CDS-T1-GE3	SI2333CDS-T1-GE3	SI2333DDS-T1-E3	SI2333DDS-T1-GE3	SI2333DDS-T1-GE3
SI2333DS	SI2333DS-T1-E3	SI2333DS-T1-E3	SI2333DS-T1-GE3	SI2333DS-T1-GE3
SI2334DS-T1-E3	SI2334DS-T1-GE3	SI2334DS-T1-GE3	SI2335DS-T1	SI2335DS-T1-E3
SI2335DS-T1-E3	SI2335DS-T1-GE3	SI2335DS-T1-GE3	SI2336DS-T1-E3	SI2336DS-T1-GE3

Contact us: Info@Y-IC.com

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